

# Silicon Carbide (SiC) Schottky Diode – EliteSiC, 30 A, 1200 V, D1, Die

## PCFFS30120AF

### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature dependent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size and cost.

### Features

- Max Junction Temperature 175°C
- Avalanche Rated 361 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery

### Applications

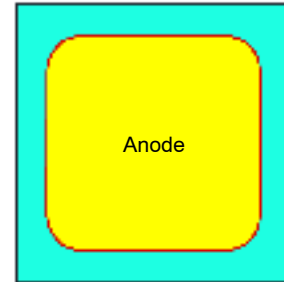
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

### Die Information

- Wafer Diameter: 6 inch
- Die Size: 3,700 × 3,700 μm (include Scribe Lane)
- Metallization:
  - ◆ Top Ti/TiN/AlCu 4 μm
  - ◆ Back Ti/NiV/Ag
- Die Thickness: Typ. 200 μm
- Bonding Pad Size
  - ◆ Anode 3,120 × 3,120 μm
- Recommended Wire Bond (Note 1)
  - ◆ Anode: 20 mil × 3

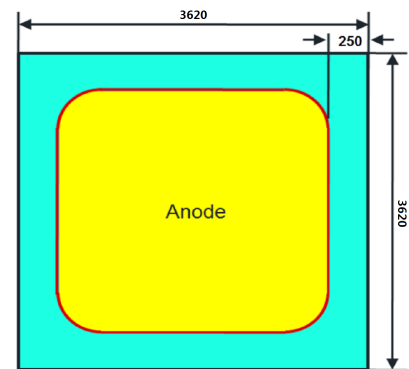
### NOTE:

1. Based on TO-247 package of onsemi.



### DIE LAYOUT

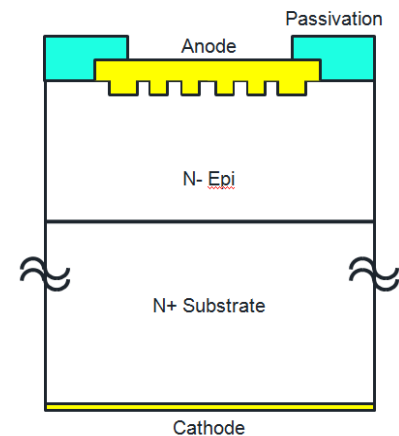
(Dimension: μm, Except Scribe Lane)



### Passivation Information

- Passivation Material: Polyimide (PSPI)
- Passivation Type: Local Passivation
- Passivation Thickness: 90KA

### CROSS SECTION



### ORDERING INFORMATION

| Part Number  | Package | Die Size                                  |
|--------------|---------|-------------------------------------------|
| PCFFS30120AF | N/A     | 3,700 × 3,700 μm<br>(Include Scribe Lane) |

# PCFFS30120AF

## ELECTRICAL CHARACTERISTICS ON WAFER ( $T_C = 25^\circ\text{C}$ unless otherwise noted) (Note 2)

| Symbol | Parameter                | Test Condition                                      | Min  | Typ | Max  | Unit          |
|--------|--------------------------|-----------------------------------------------------|------|-----|------|---------------|
| $V_R$  | Reverse Blocking Voltage | $I_R = 200\ \mu\text{A}$ , $T_C = 25^\circ\text{C}$ | 1200 | –   | –    | V             |
| $V_F$  | Forward Voltage          | $I_F = 30\ \text{A}$ , $T_C = 25^\circ\text{C}$     | 1.20 | –   | 1.75 | V             |
| $I_R$  | Reverse Current          | $V_R = 1200\ \text{V}$ , $T_C = 25^\circ\text{C}$   | –    | –   | 200  | $\mu\text{A}$ |

2. Tested 100% on wafer.

### The Configuration of Chips (Based on 6" Wafer)

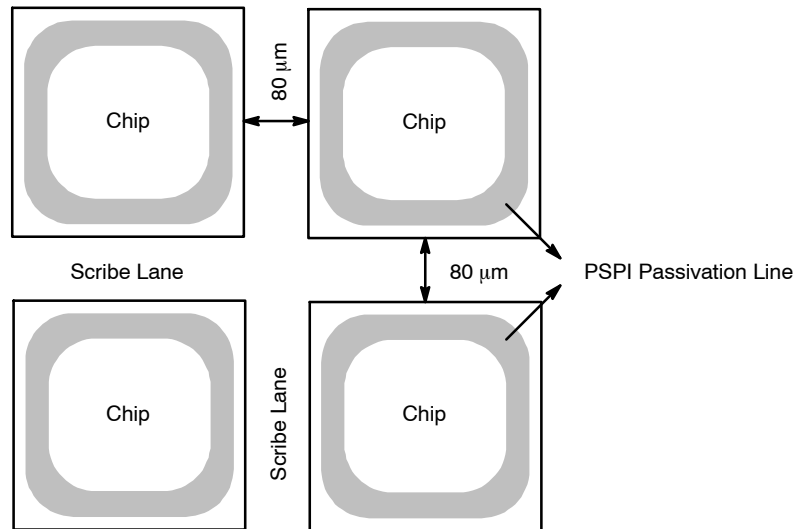


Figure 1. Saw-on-film Frame Packing Based on Tested Wafer

# PCFFS30120AF

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

| Symbol                            | Parameter                                                     | FFSH30120A                               | Unit |
|-----------------------------------|---------------------------------------------------------------|------------------------------------------|------|
| V <sub>RRM</sub>                  | Peak Repetitive Reverse Voltage                               | 1200                                     | V    |
| E <sub>AS</sub>                   | Single Pulse Avalanche Energy (Note 3)                        | 361                                      | mJ   |
| I <sub>F</sub>                    | Continuous Rectified Forward Current @ T <sub>C</sub> < 155°C | 30                                       | A    |
|                                   | Continuous Rectified Forward Current @ T <sub>C</sub> < 135°C | 46                                       |      |
| I <sub>F, Max</sub>               | Non-Repetitive Peak Forward Surge Current                     | T <sub>C</sub> = 25°C, 10 μs             | A    |
|                                   |                                                               | T <sub>C</sub> = 150°C, 10 μs            | A    |
| I <sub>F, SM</sub>                | Non-Repetitive Forward Surge Current                          | Half-Sine Pulse, t <sub>p</sub> = 8.3 ms | A    |
| I <sub>F, RM</sub>                | Repetitive Forward Surge Current                              | Half-Sine Pulse, t <sub>p</sub> = 8.3 ms | A    |
| P <sub>tot</sub>                  | Power Dissipation                                             | T <sub>C</sub> = 25°C                    | W    |
|                                   |                                                               | T <sub>C</sub> = 150°C                   | W    |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature Range                       | -55 to +175                              | °C   |
|                                   | TO247 Mounting Torque, M3 Screw                               | 60                                       | Ncm  |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

3. E<sub>AS</sub> of 361 mJ is based on starting T<sub>J</sub> = 25°C, L = 0.5 mH, I<sub>AS</sub> = 38 A, V = 50 V.

## THERMAL CHARACTERISTICS

| Symbol           | Parameter                                 | Value | Unit |
|------------------|-------------------------------------------|-------|------|
| R <sub>θJC</sub> | Thermal Resistance, Junction to Case, Max | 0.3   | °C/W |

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

| Symbol         | Parameter               | Test Condition                                  | Min | Typ  | Max  | Unit |
|----------------|-------------------------|-------------------------------------------------|-----|------|------|------|
| V <sub>F</sub> | Forward Voltage         | I <sub>F</sub> = 30 A, T <sub>C</sub> = 25°C    | –   | 1.45 | 1.75 | V    |
|                |                         | I <sub>F</sub> = 30 A, T <sub>C</sub> = 125°C   | –   | 1.7  | 2.0  |      |
|                |                         | I <sub>F</sub> = 30 A, T <sub>C</sub> = 175°C   | –   | 2.0  | 2.4  |      |
| I <sub>R</sub> | Reverse Current         | V <sub>R</sub> = 1200 V, T <sub>C</sub> = 25°C  | –   | –    | 200  | μA   |
|                |                         | V <sub>R</sub> = 1200 V, T <sub>C</sub> = 125°C | –   | –    | 300  |      |
|                |                         | V <sub>R</sub> = 1200 V, T <sub>C</sub> = 175°C | –   | –    | 400  |      |
| Q <sub>C</sub> | Total Capacitive Charge | V = 800 V                                       | –   | 175  | –    | nC   |
| C              | Total Capacitance       | V <sub>R</sub> = 1 V, f = 100 kHz               | –   | 1740 | –    | pF   |
|                |                         | V <sub>R</sub> = 400 V, f = 100 kHz             | –   | 159  | –    |      |
|                |                         | V <sub>R</sub> = 800 V, f = 100 kHz             | –   | 130  | –    |      |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

**TYPICAL CHARACTERISTICS**  
( $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)

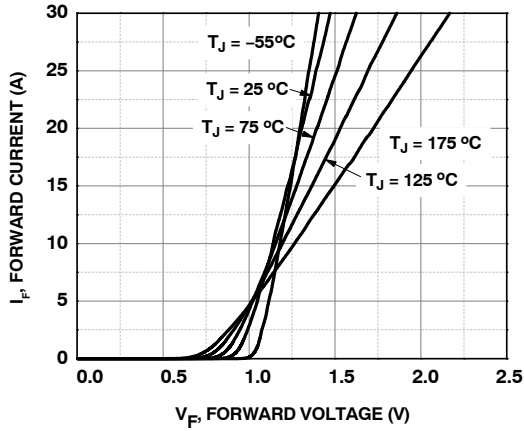


Figure 2. Forward Characteristics

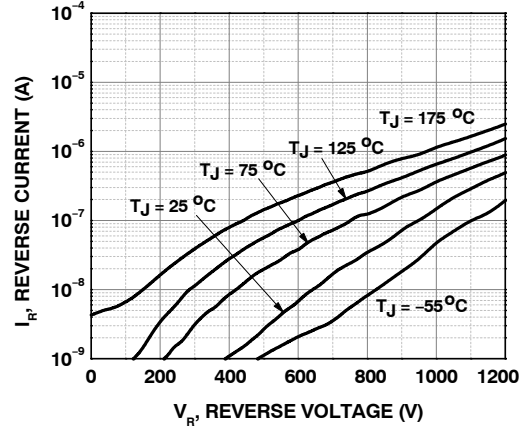


Figure 3. Reverse Characteristics

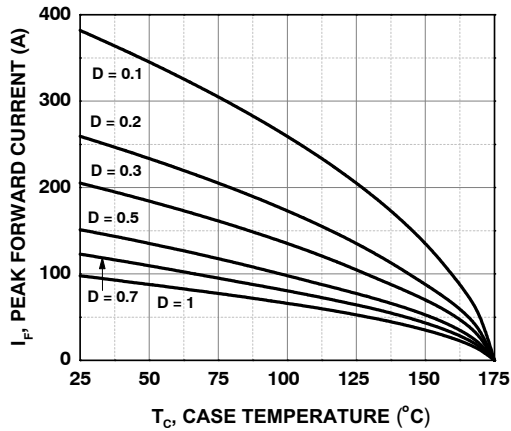


Figure 4. Current Derating

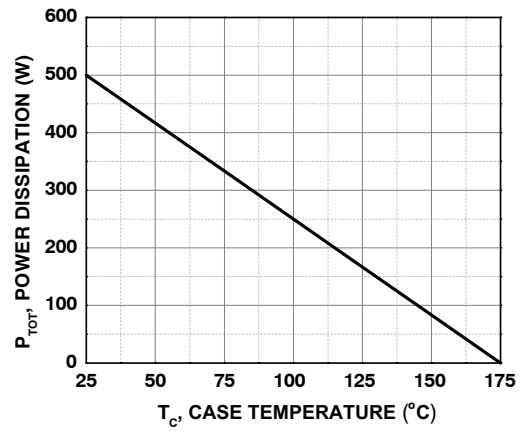


Figure 5. Power Derating

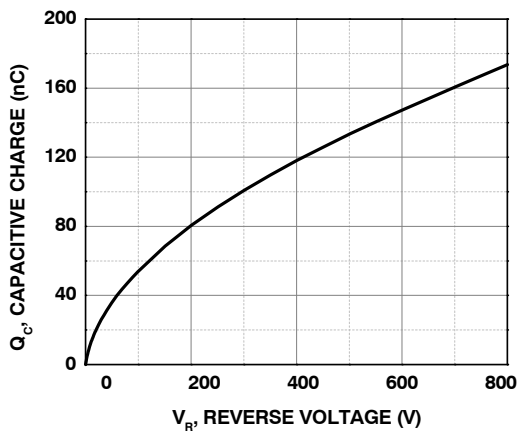


Figure 6. Capacitive Charge vs. Reverse Voltage

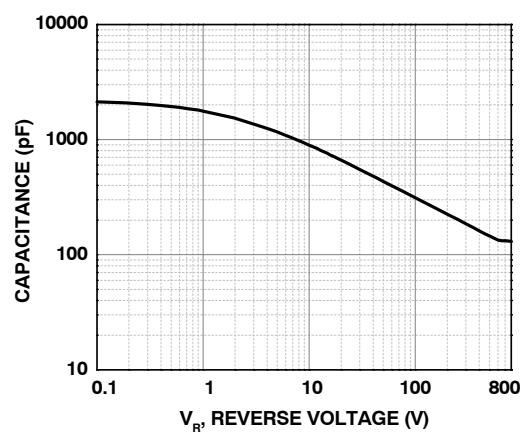


Figure 7. Capacitive vs. Reverse Voltage

**TYPICAL CHARACTERISTICS**  
( $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)

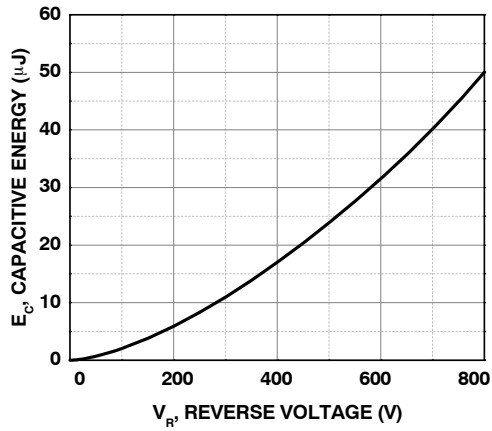


Figure 8. Capacitance Stored Energy

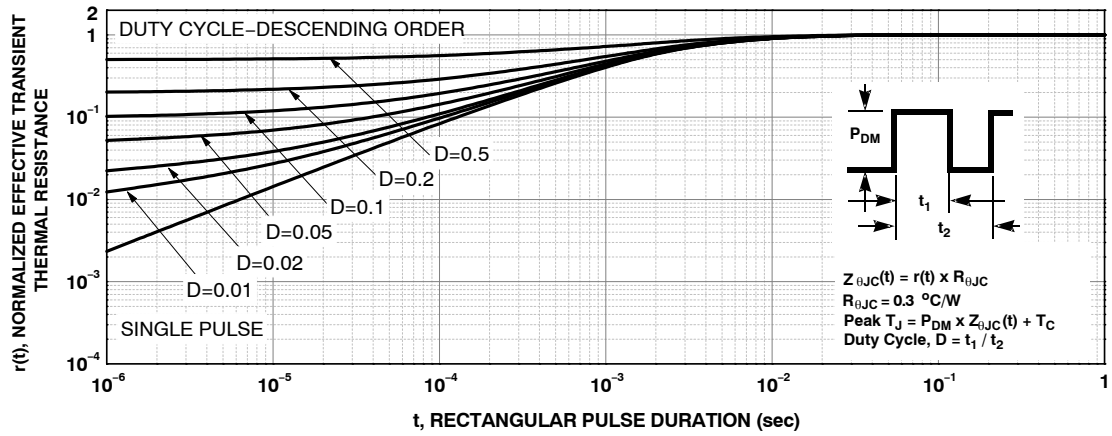


Figure 9. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

$L = 0.5 \text{ mH}$   
 $R < 0.1 \Omega$   
 $V_{DD} = 50 \text{ V}$   
 $E_{AVL} = 1/2 L I_L^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$   
 $Q1 = \text{IGBT (} BV_{CES} > \text{DUT } V_{R(AVL)} \text{)}$

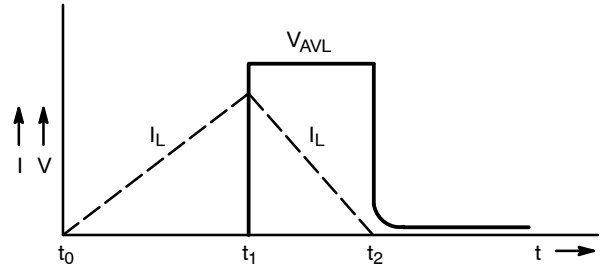
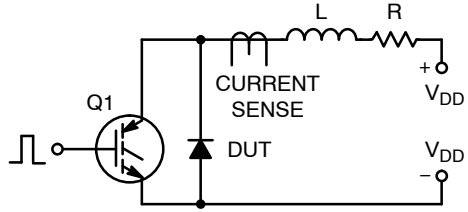


Figure 10. Unclamped Inductive Switching Test Circuit & Waveform

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